

PNP High Voltage Amplifier

This device is designed for high voltage driver applications. Sourced from Process 76.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CEO}	Collector-Emitter Voltage	300	V	
V _{CBO}	Collector-Base Voltage	300	V	
V _{EBO}	Emitter-Base Voltage	5.0	V	
l _c	Collector Current - Continuous	500	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах		Units	
		MPSA92	*MMBTA92	**PZTA92	
PD	Total Device Dissipation	625	350	1,000	mW
	Derate above 25°C	5.0	2.8	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

PNP High Voltage Amplifier (c

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Electrical Characteristics TA = 25°C unless otherwise noted						
Symbol	Parameter Test Conditions M		Min	Max	Units	
OFF CHA	RACTERISTICS					
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	300		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	300		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \ \mu {\rm A}, \ I_{\rm C} = 0$	5.0		V	
СВО	Collector-Cutoff Current	$V_{CB} = 200 \text{ V}, I_E = 0$		0.25	μΑ	
EBO	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}$. $I_{C} = 0$		0.1	μA	

ON CHARACTERISTICS*

h _{FE}	DC Current Gain	I _C = 1.0 mA, V _{CE} = 10 V	25		
		$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	40		
		$I_{C} = 30 \text{ mA}, V_{CE} = 10 \text{ V}$	25		
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 20$ mA, $I_{\rm B} = 2.0$ mA		0.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 20$ mA, $I_{\rm B} = 2.0$ mA		0.9	V

SMALL SIGNAL CHARACTERISTICS

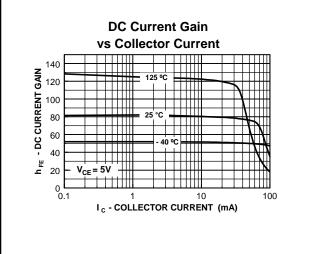
f⊤	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	50		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		6.0	pF

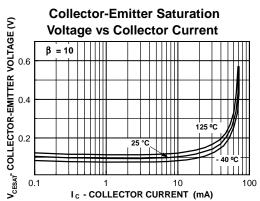
*Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%

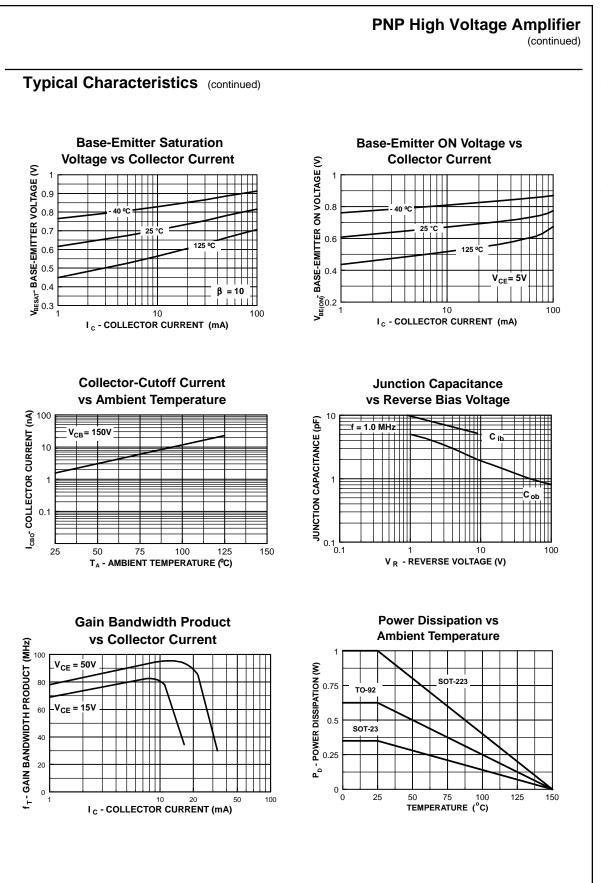
Spice Model

PNP (Is=218.9f Xti=3 Eg=1.11 Vaf=100 Bf=99 Ne=1.307 Ise=218.9f Ikf=.2016 Xtb=1.5 Br=24.67 Nc=2 Isc=0 Ikr=0 Rc=7 Cjc=19.88p Mjc=.4876 Vjc=.75 Fc=.5 Cje=81.49p Mje=.3493 Vje=.75 Tr=516.9p Tf=1.395n Itf=1.5 Vtf=22 Xtf=270 Rb=10)

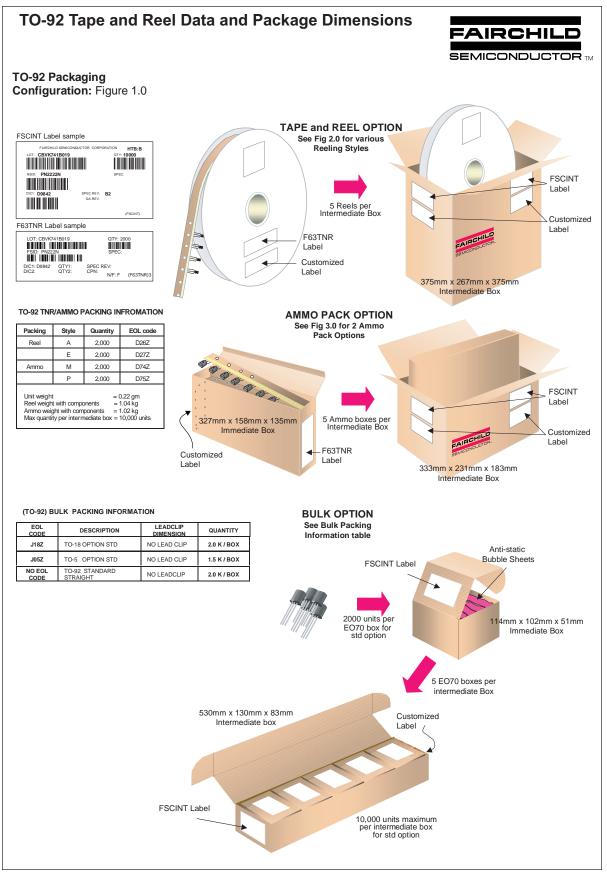
Typical Characteristics



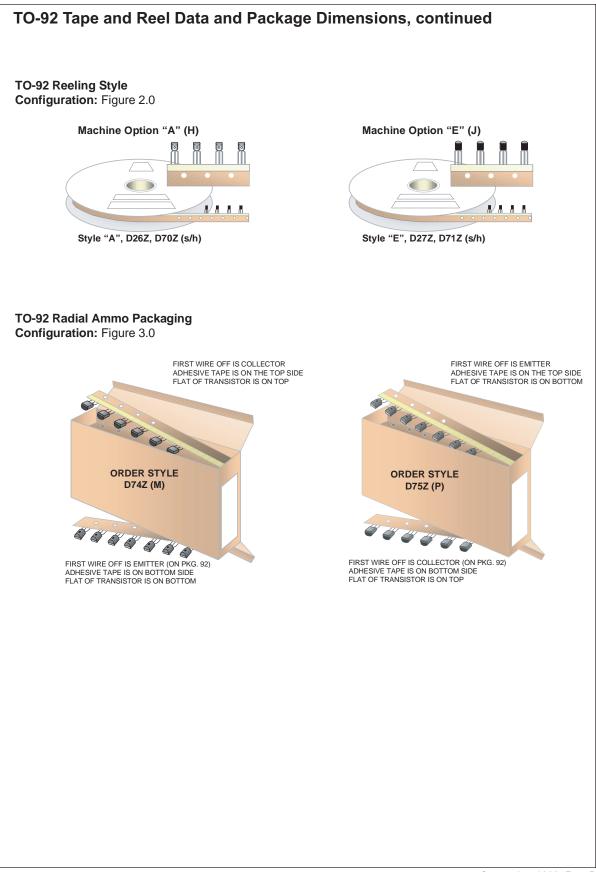


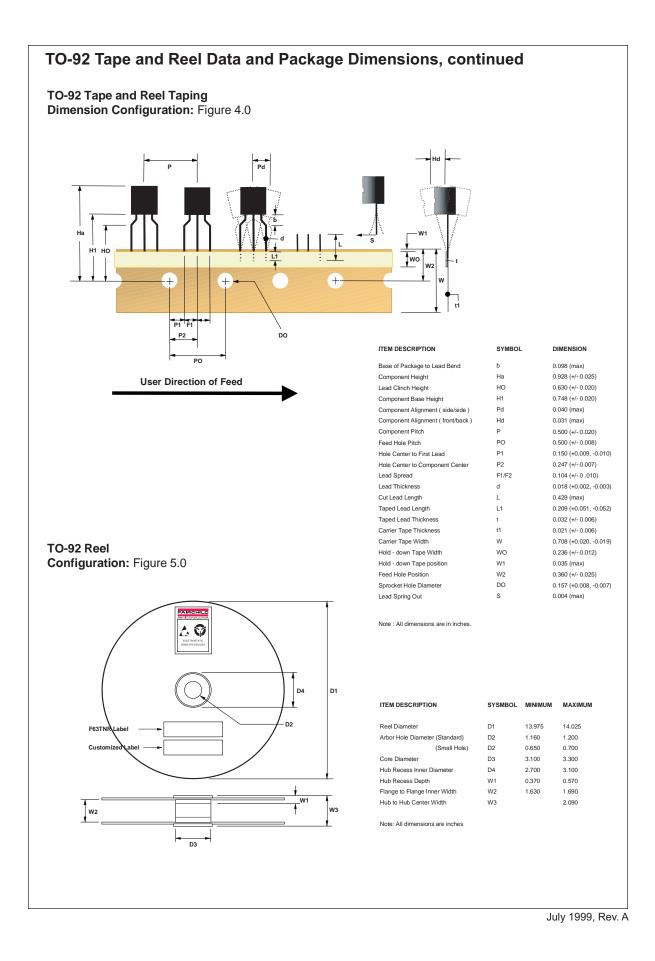


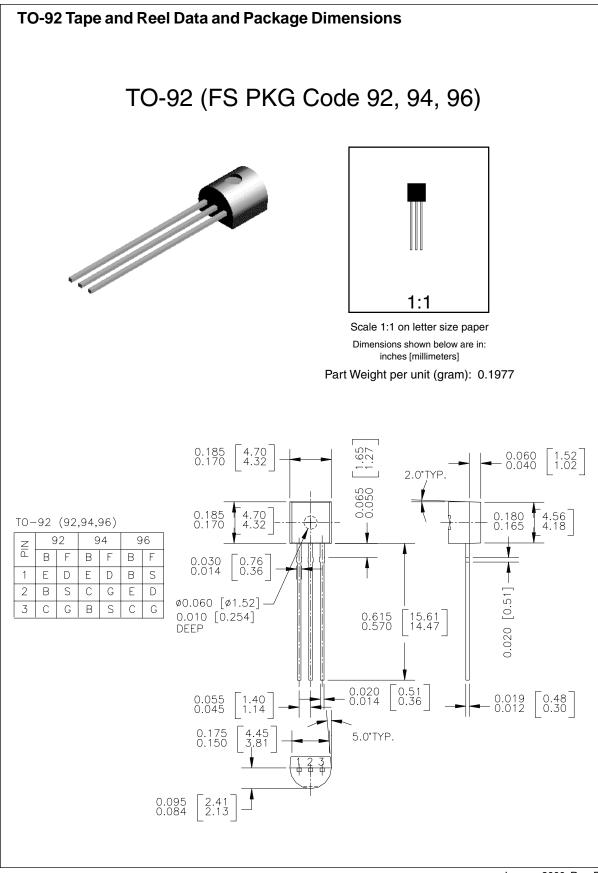
MPSA92 / MMBTA92 / PZTA92



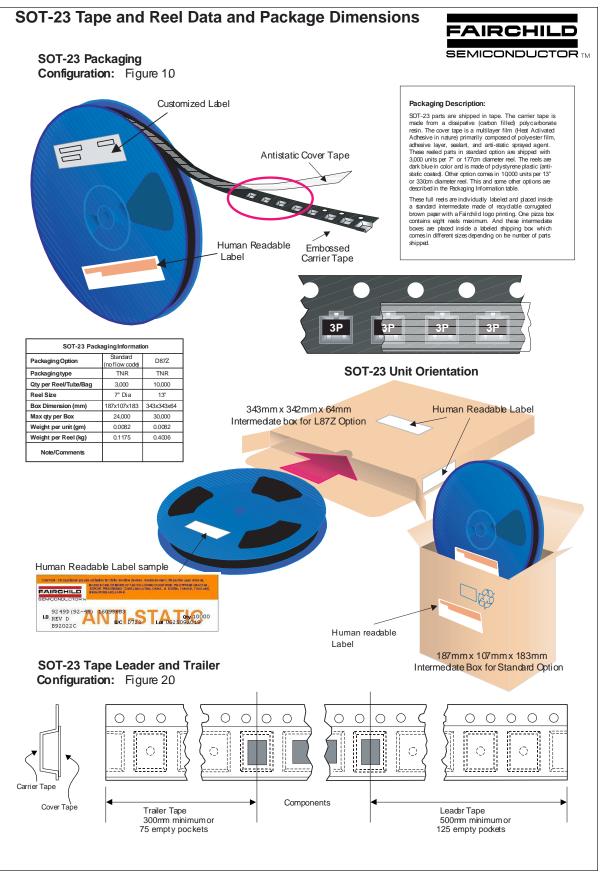
September 1999, Rev. B



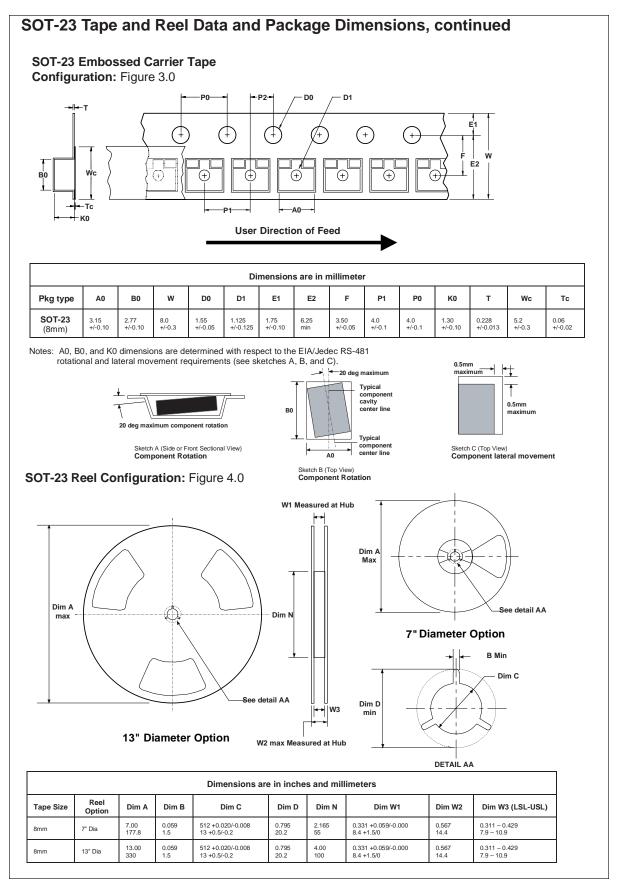




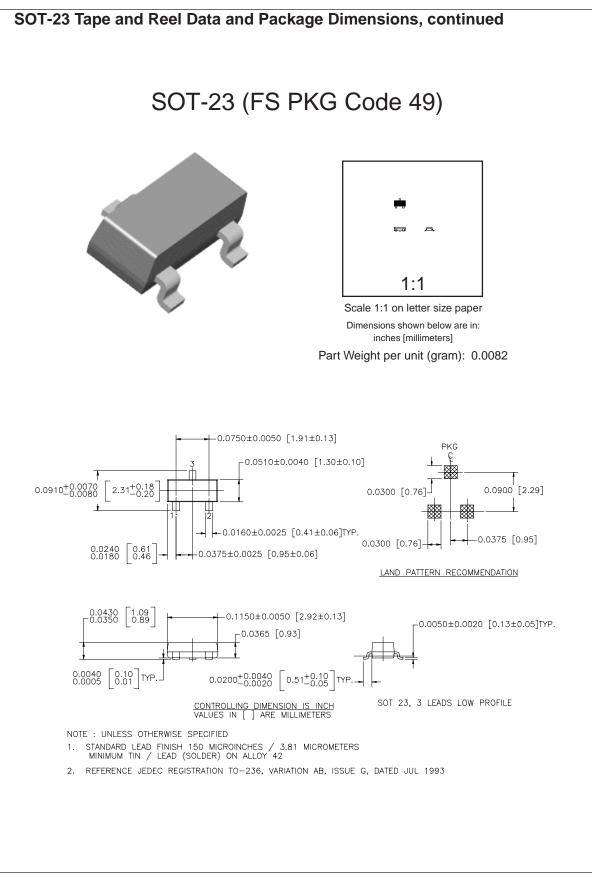
January 2000, Rev. B



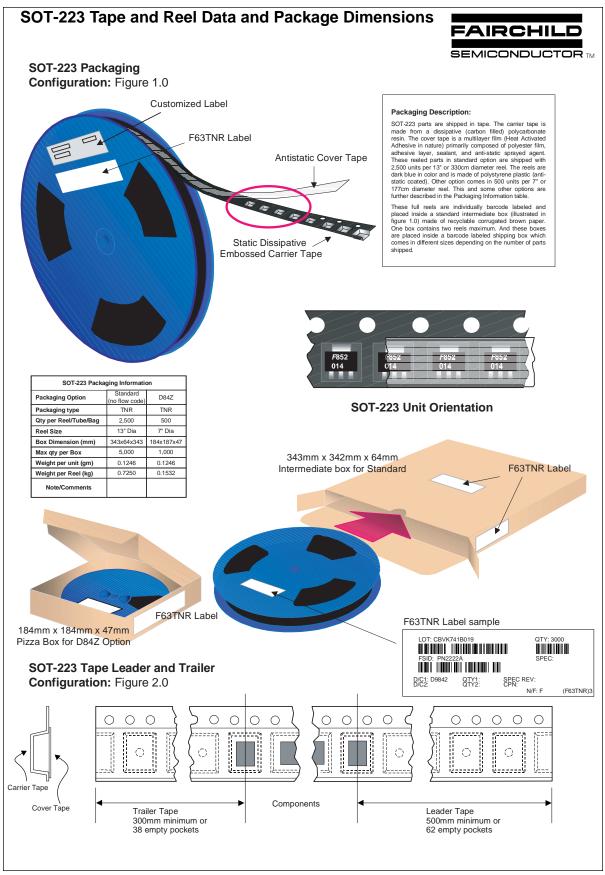
September 1999, Rev. C



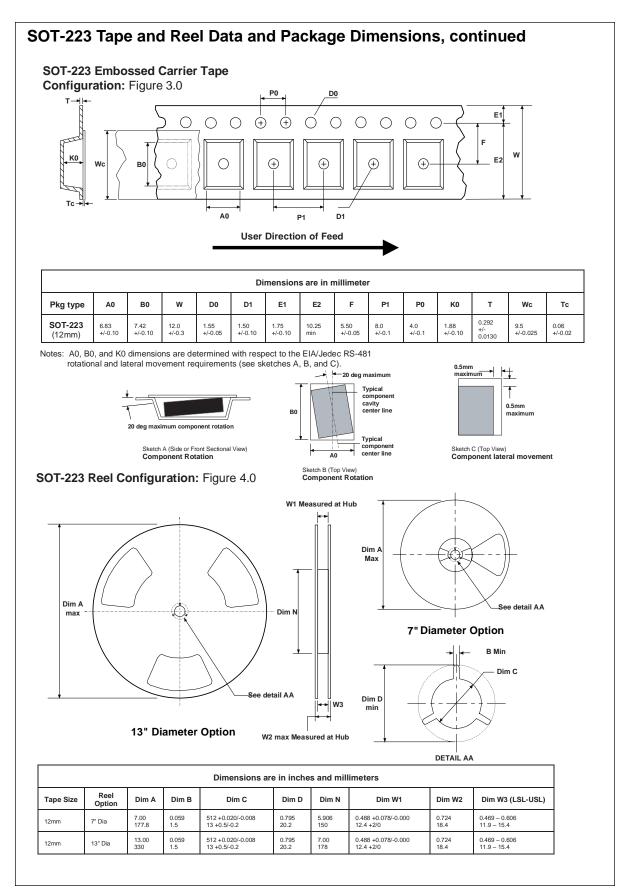
September 1999, Rev. C

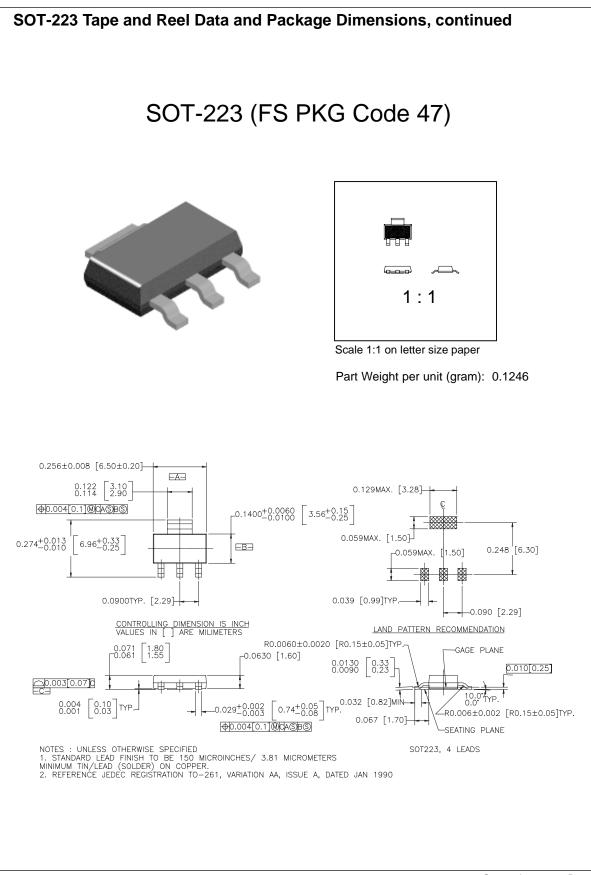


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September 1999, Rev. B





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